

Features

- $BV_{CEO} > -100V$
- $BV_{ECO} > -7V$
- $I_C = -1A$ Continuous Collector Current
- $I_{CM} = -3A$ Peak Collector Current
- $V_{CE(SAT)} < -225mV @ -1A$
- $R_{CE(SAT)} = 155m\Omega$ for a Low Equivalent On-Resistance
- Complementary NPN Type: ZXTN25100DZ
- **Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

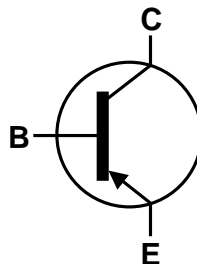
Mechanical Data

- Case: SOT89
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Plated Leads. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.05 grams (Approximate)

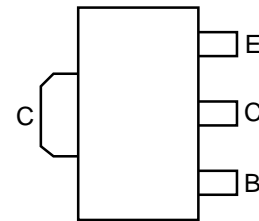
SOT89



Top View



Device Symbol



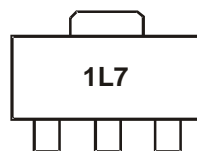
Top View
Pin Out

Ordering Information (Note 4)

Product	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
ZXTP25100CZTA	AEC-Q101	1L7	7	12	1,000

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



1L7 = Product Type Marking Code

Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Limit	Unit
Collector-Base Voltage	V _{CBO}	-115	V
Collector-Emitter Voltage	V _{CEO}	-100	V
Emitter-Collector Voltage (Reverse Blocking)	V _{ECO}	-7	V
Emitter-Base Voltage	V _{EBO}	-7	V
Continuous Collector Current	I _C	-1	A
Peak Pulse Current	I _{CM}	-3	A
Base Current	I _B	-500	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

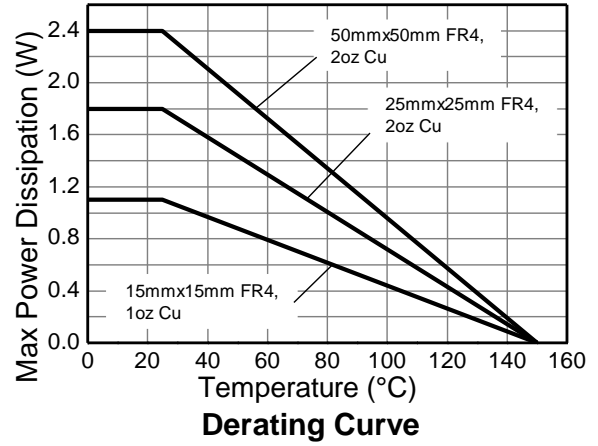
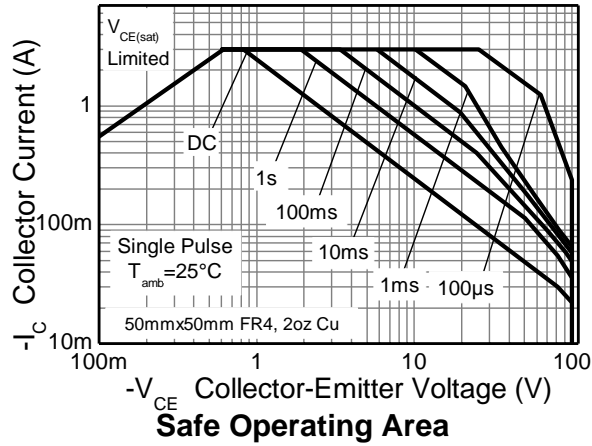
Characteristic	Symbol	Value	Unit
Power Dissipation Linear Derating Factor	P _D	1.1	W mW/°C
		8.8	
		1.8	
		14.4	
		2.4	
Thermal Resistance, Junction to Ambient Air	R _{θJA}	19.2	°C/W
		4.46	
		35.7	
		117	
Thermal Resistance, Junction to Lead	R _{θJL}	68	°C/W
		51	
		28	
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

ESD Ratings (Note 10)

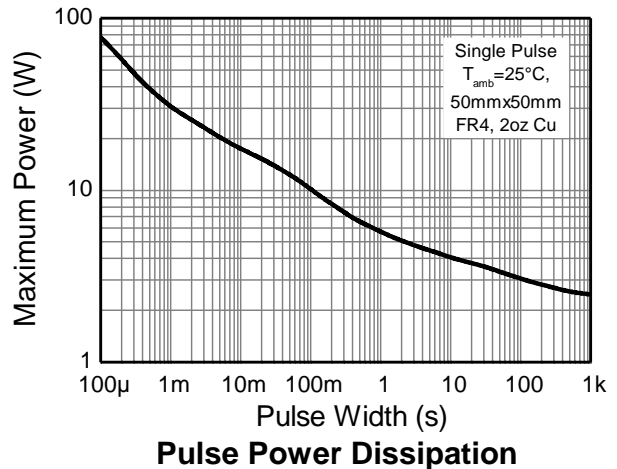
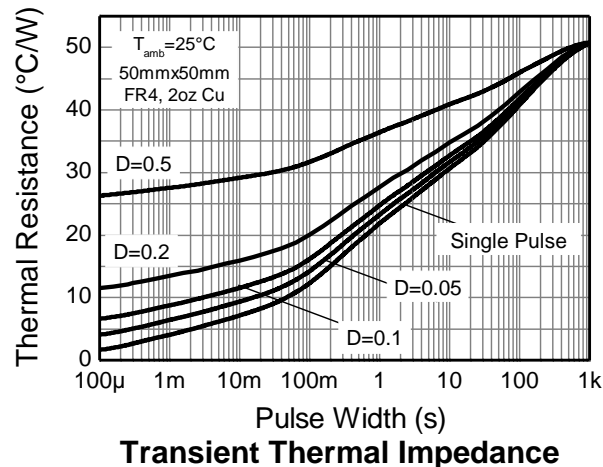
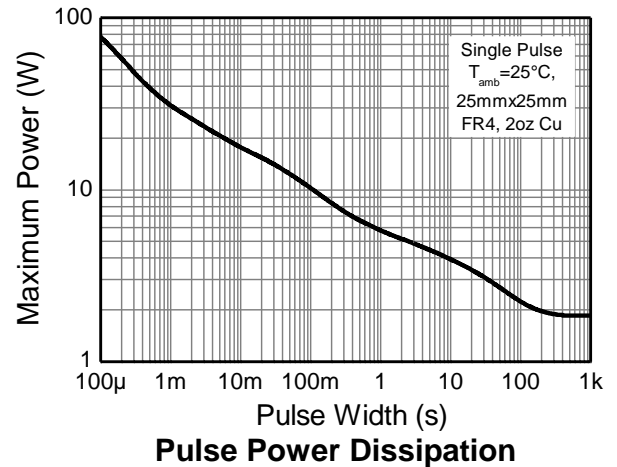
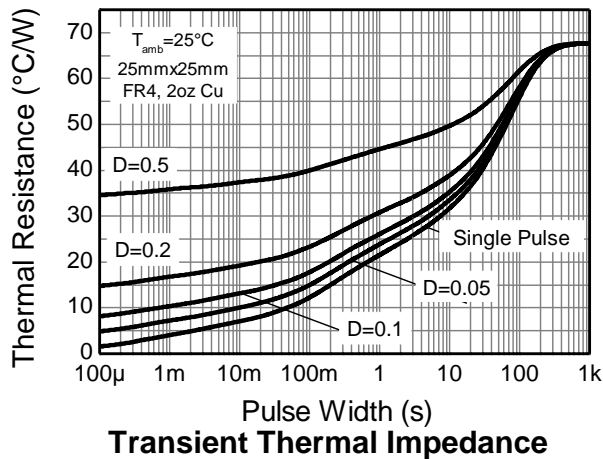
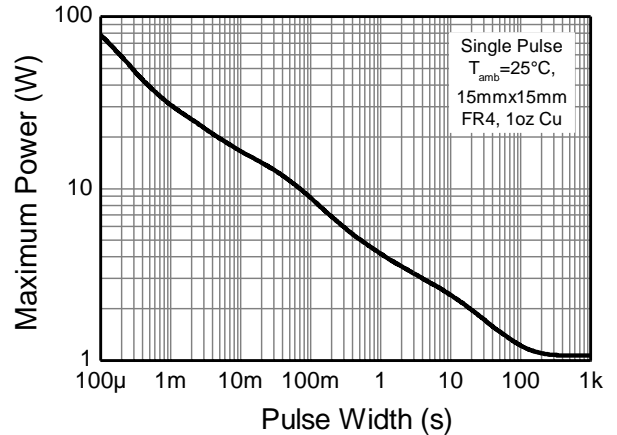
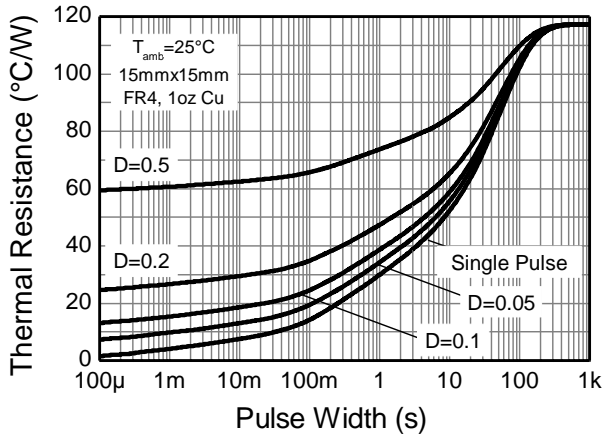
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge – Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge – Machine Model	ESD MM	400	V	C

- Notes:
- For a device mounted with the exposed collector pad on 15mm x 15mm 1oz copper that is on a single-sided 0.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
 - Same as Note 5, except the device is mounted on 25mm x 25mm 2oz copper.
 - Same as Note 5, except the device is mounted on 50mm x 50mm 2oz copper.
 - Same as Note 7, except the device is measured at t<5 seconds.
 - Thermal resistance from junction to solder-point (on the exposed collector pad).
 - Refer to JEDEC specification JESD22-A114 and JESD22-A115.

Thermal Characteristics and Derating Information



Thermal Characteristics and Derating Information (Continued)

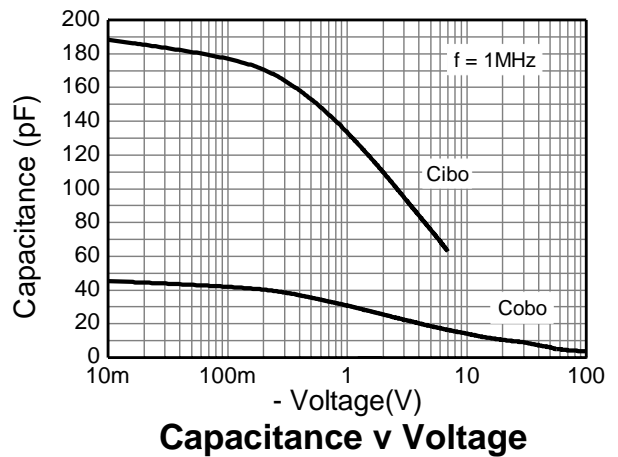
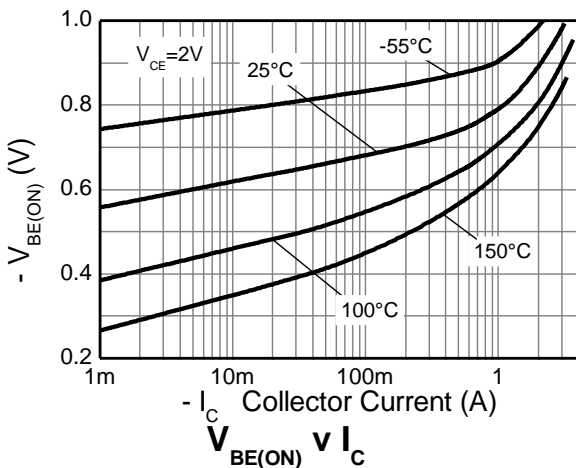
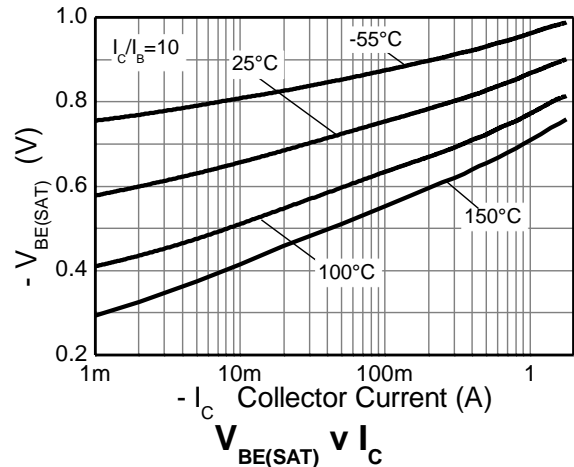
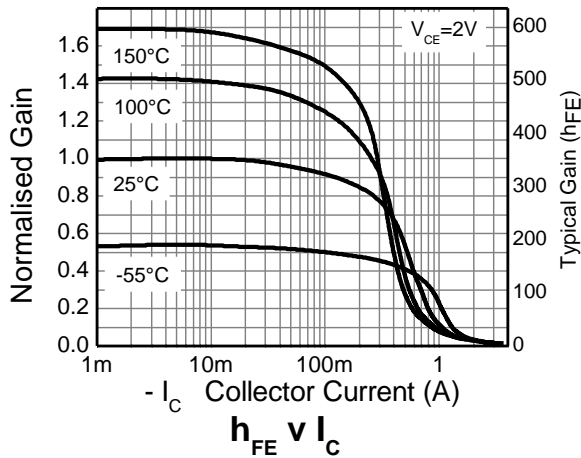
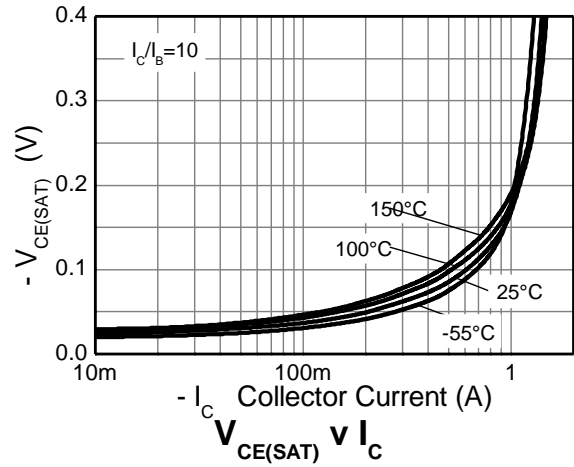
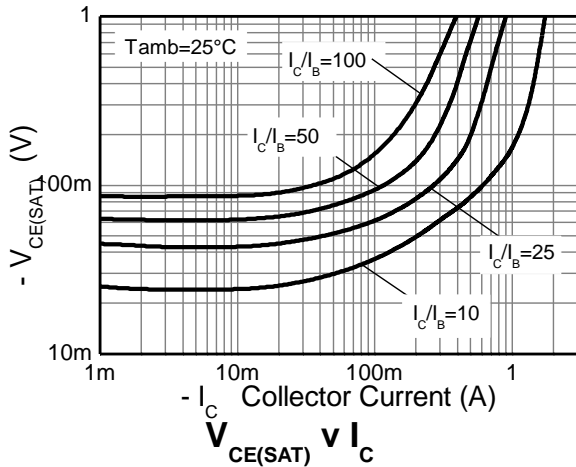


Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	-115	-180	—	V	I _C = -100μA
Collector-Emitter Breakdown Voltage (Note 11)	BV _{CEO}	-100	-140	—	V	I _C = -10mA
Emitter-Collector Breakdown Voltage (reverse blocking)	BV _{ECX}	-7	-8.3	—	V	I _E = -100μA, R _{BC} <1kΩ or -0.25V > V _{BC} > 0.25V
Emitter-Collector Breakdown Voltage (Reverse Blocking)	BV _{ECO}	-7	-8.8	—	V	I _E = -100μA
Emitter-Base Breakdown Voltage	BV _{EBO}	-7	-8.4	—	V	I _E = -100μA
Collector-Base Cutoff Current	I _{CBO}	—	<-1	-50 -0.5	nA μA	V _{CB} = -115V V _{CB} = -115V, T _A = +100°C
Collector-Emitter Cutoff Current	I _{CEX}	—	—	-100	nA	V _{CE} = -90V, R _{BE} <1kΩ or -0.25V < V _{BE} < 1V
Emitter Cutoff Current	I _{EBO}	—	<1	-50	nA	V _{EB} = -5.6V
DC current transfer Static ratio (Note 11)	h _{FE}	200 180 110 20	350 320 190 35	500 — — —	—	I _C = -10mA, V _{CE} = -2V I _C = -100mA, V _{CE} = -2V I _C = -500mA, V _{CE} = -2V I _C = -1A, V _{CE} = -2V
Collector-Emitter Saturation Voltage (Note 11)	V _{CE(SAT)}	—	-140 -80 -180 -155	-210 -115 -315 -225	mV	I _C = -100mA, I _B = -1mA I _C = -500mA, I _B = -50mA I _C = -500mA, I _B = -20mA I _C = -1A, I _B = -100mA
Base-Emitter Saturation Voltage (Note 11)	V _{BE(SAT)}	—	-860	-950	mV	I _C = -1A, I _B = -100mA
Base-Emitter Turn-On Voltage (Note 11)	V _{BE(ON)}	—	-800	-900	mV	I _C = -1A, V _{CE} = -2V
Transitional Frequency	f _T	—	180	—	MHz	I _E = -20mA, V _{CE} = -15V f = 100MHz
Input Capacitance	C _{IBO}	—	153	—	pF	V _{EB} = -0.5V, f = 1MHz,
Output Capacitance	C _{OBO}	—	14.1	20	pF	V _{CB} = -10V, f = 1MHz,
Delay Time	t _D	—	15.8	—	ns	I _C = -500mA, V _{CC} = -10V, I _{B1} = -I _{B2} = -50mA
Rise Time	t _R	—	41	—	ns	
Storage Time	t _S	—	411	—	ns	
Fall Time	t _F	—	89	—	ns	

Note: 11. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%.

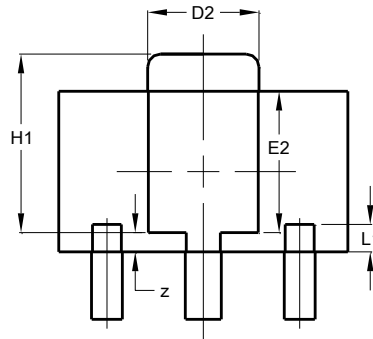
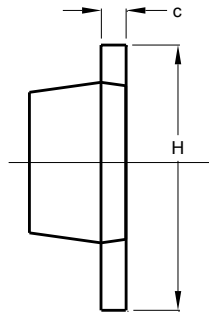
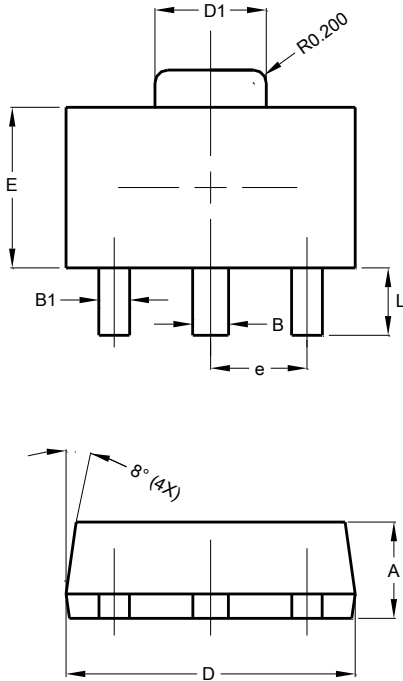
Typical Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)



Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT89

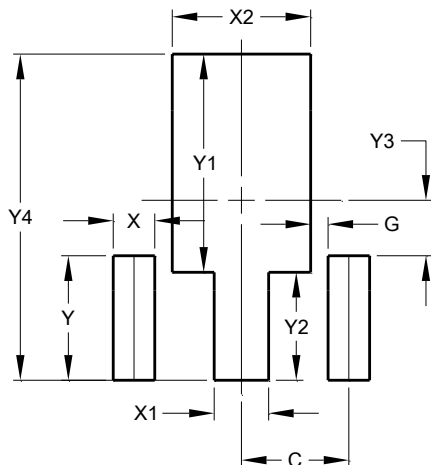


SOT89			
Dim	Min	Max	Typ
A	1.40	1.60	1.50
B	0.50	0.62	0.56
B1	0.42	0.54	0.48
c	0.35	0.43	0.38
D	4.40	4.60	4.50
D1	1.62	1.83	1.733
D2	1.61	1.81	1.71
E	2.40	2.60	2.50
E2	2.05	2.35	2.20
e	-	-	1.50
H	3.95	4.25	4.10
H1	2.63	2.93	2.78
L	0.90	1.20	1.05
L1	0.327	0.527	0.427
z	0.20	0.40	0.30
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT89



Dimensions	Value (in mm)
C	1.500
G	0.244
X	0.580
X1	0.760
X2	1.933
Y	1.730
Y1	3.030
Y2	1.500
Y3	0.770
Y4	4.530

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device Terminals and PCB tracking.

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